

Notice of References Cited	Application/Control No. 09/745,114		Applicant(s)/Patent Under Reexamination YANG, SAM	
	Examiner Scott R. Wilson		Art Unit 2826	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-4,937,650	06-1990	Shinriki et al.	257/296
	B	US-5,558,961	09-1996	Doeff et al.	429/224
	C	US-4,899,203	02-1990	Ino, Masayoshi	257/306
	D	US-5,856,937	01-1999	Chu et al.	365/51
	E	US-5,867,444	02-1999	Le et al.	365/230.06
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	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
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	R					
	S					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)			
	U	Time Domain CVD, http://www.timedomaincvd.com/CVD_Fundamentals/films/Ta2O5.html , High Dielectric constant Materials for DRAMS: Tantalum Oxide. Chart listing dielectric constants of SiO2, Si3N4, Ta2O5, BST			
	V				
	W				
	X				

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.